

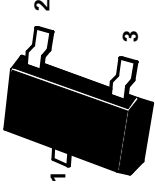
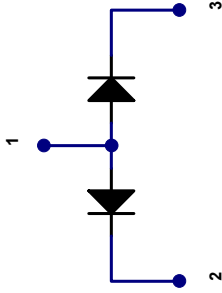
FLLD258
FLLD261
FLLD263

**SOT23 SILICON PLANAR LOW LEAKAGE
COMMON ANODE DIODE PAIR**

ISSUE 2 – JANUARY 1996

FLLD263

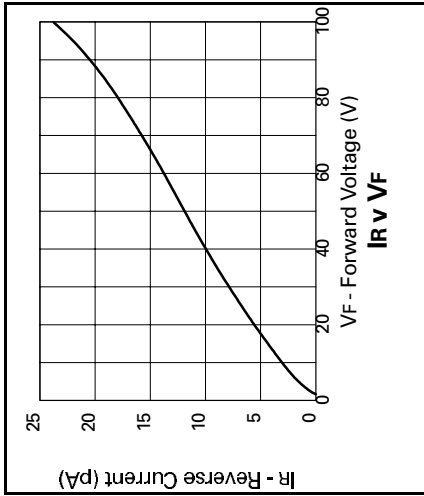
DIODE PIN CONNECTION



SOT23

PART MARKING DETAIL – D63

TYPICAL CHARACTERISTICS



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Average Rectified Forward Current	$I_{F(AV)}$	250	mA
Non-Repetitive Peak Forward Current ($t=1\mu s$)	I_{FSM}	3.0	A
Power Dissipation at $T_{amb} = 25^{\circ}C$	P_{tot}	330	mW
Operating and Storage Temperature Range	T_j, T_{stg}	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Reverse Current	I_R		5	nA	$V_{RRMF}=100V$
			5	μA	$V_{RRMF}=100V, T_{amb}=150^{\circ}C$
Reverse Recovery Time*	t_{rr}		400	ns	$I_F=I_R=50 - 400mA$
Forward Recovery Time	t_{fr}		10	ns	$I_F=10mA$
Diode Capacitance	C_d		4	pF	$V_R=1V, f=1MHz$
Forward Overshoot Voltage	V_{fr}		Typ 0.9	V	$I_F=10mA,$ Rise time=5ns $\pm 20\%$
Forward Voltage	V_F		1.4	V	$I_F=200mA$

*Time for I_R to recover to 10% of I_R peak

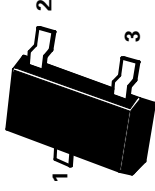
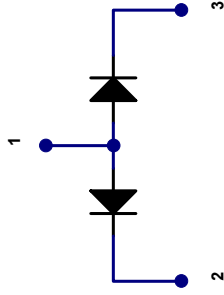
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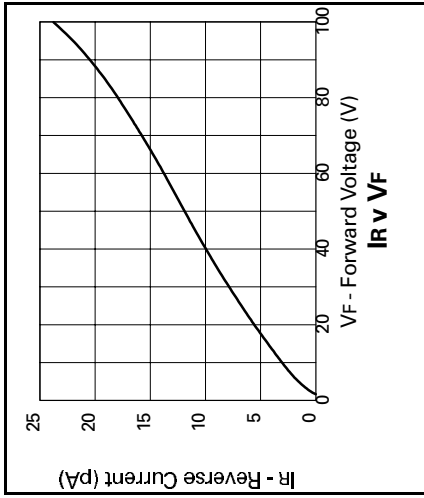
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